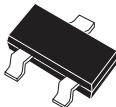


**CMPF4391
CMPF4392
CMPF4393**

N-CHANNEL JFET



SOT-23 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPF4391 series types are N-Channel Silicon Field Effect Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for switching applications.

Marking Codes are 6J, 6K, and 6G Respectively.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Drain-Gate Voltage	V _{GD}	40	V
Gate-Source Voltage	V _{GS}	40	V
Drain-Source Voltage	V _{DS}	40	V
Gate Current	I _G	50	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPF4391		CMPF4392		CMPF4393		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{GSS}	V _{GS} =20V		0.1		0.1		0.1	nA
I _{GSS}	V _{GS} =20V, T _A =100°C		0.2		0.2		0.2	μA
I _{DSS}	V _{DS} =20V	50	150	25	75	5.0	30	mA
I _D (OFF)	V _{DS} =20V, V _{GS} =12V		0.1		-		-	nA
I _D (OFF)	V _{DS} =20V, V _{GS} =7.0V		-		0.1		-	nA
I _D (OFF)	V _{DS} =20V, V _{GS} =5.0V		-		-		0.1	nA
I _D (OFF)	V _{DS} =20V, V _{GS} =12V, T _A =100°C		0.2		-		-	μA
I _D (OFF)	V _{DS} =20V, V _{GS} =7.0V, T _A =100°C		-		0.2		-	μA
I _D (OFF)	V _{DS} =20V, V _{GS} =5.0V, T _A =100°C		-		-		0.2	μA
BV _{GSS}	I _G =1.0μA	40		40		40		V
V _{GS} (OFF)	V _{DS} =20V, I _D =1.0nA	4.0	10	2.0	5.0	0.5	3.0	V
V _{GS} (f)	I _G =1.0mA		1.0		1.0		1.0	V
V _{DS} (ON)	I _D =12mA		0.4		-		-	V
V _{DS} (ON)	I _D =6.0mA		-		0.4		-	V
V _{DS} (ON)	I _D =3.0mA		-		-		0.4	V

